

Schottky barrier diode

RB721Q-40

●Applications

High speed switching

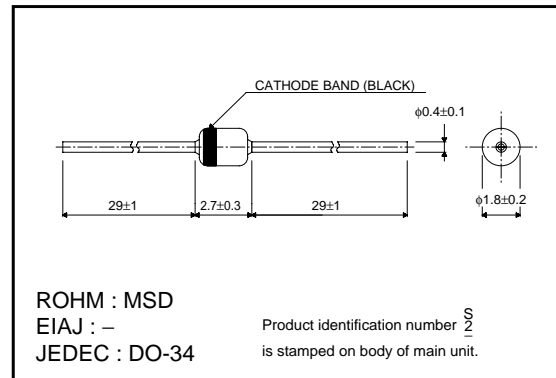
●Features

- 1) Glass-sealed envelope for high reliability. (MSD)
- 2) Small pitch enables insertion on PCBs.
- 3) Low V_F and low I_R .

●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_o	30	mA
Peak forward surge current*	I_{FSM}	200	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~+125	°C

* 60 Hz for 1 μ s

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.37	V	$I_F=1\text{mA}$
Reverse current	I_R	-	-	0.5	μA	$V_R=25\text{V}$
Capacitance between terminals	C_T	-	2.0	-	pF	$V_R=1\text{V}$, $f=1\text{MHz}$

Note) ESD sensitive product handling required.

Diodes

●Electrical characteristic curves (Ta=25°C)

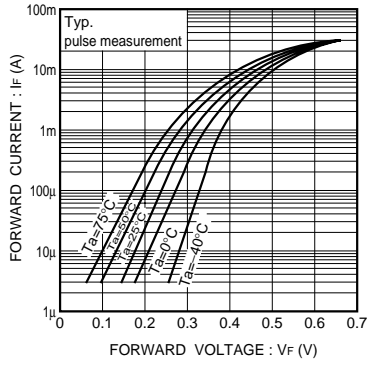


Fig.1 Forward characteristics

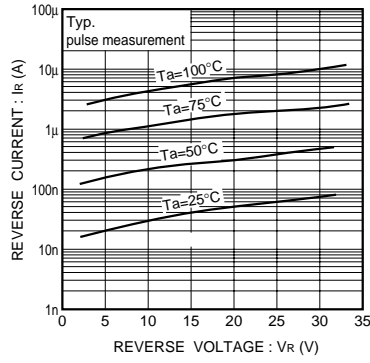


Fig.2 Reverse characteristics

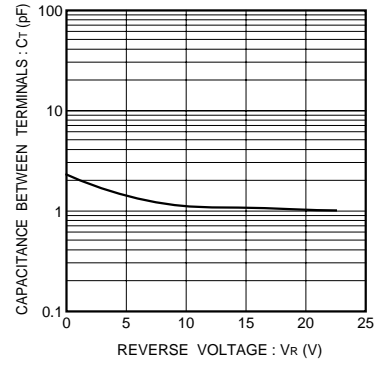


Fig.3 Capacitance between terminals characteristics

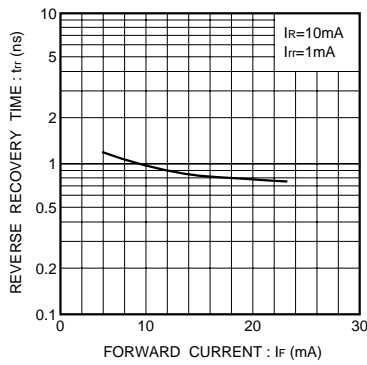


Fig.4 Reverse recovery time characteristics

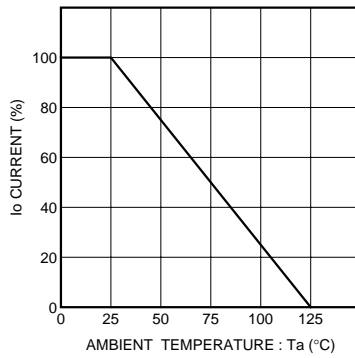


Fig.5 Derating curve (mounting on glass epoxy PCBs)